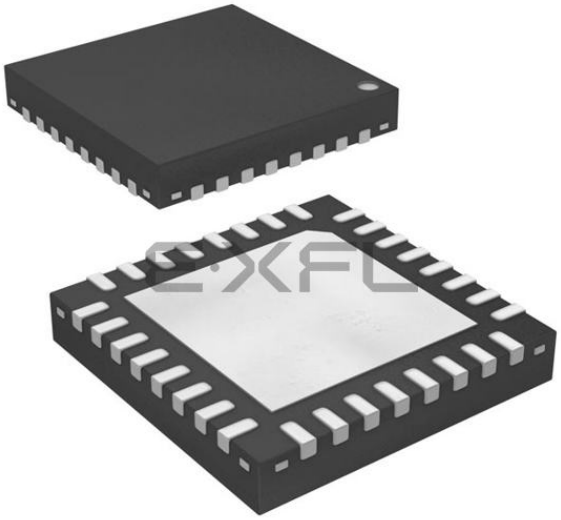
Renesas Electronics America Inc - R5F10JBCGNA#U0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART, USB
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	5.5K x 8
Voltage - Supply (Vcc/Vdd)	2.4V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10jbcgna-u0

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P137, P140, $\overline{\text{RESET}}$	$V_I = V_{DD}$				1	μA
	I_{LIH2}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	$V_I = V_{DD}$	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	I_{LIL1}	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P137, P140, $\overline{\text{RESET}}$	$V_I = V_{SS}$				–1	μA
	I_{LIL2}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	$V_I = V_{SS}$	In input port or external clock input			–1	μA
				In resonator connection			–10	μA
On-chip pll-up resistance	R_U	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	$V_I = V_{SS}$, In input port		10	20	100	kΩ

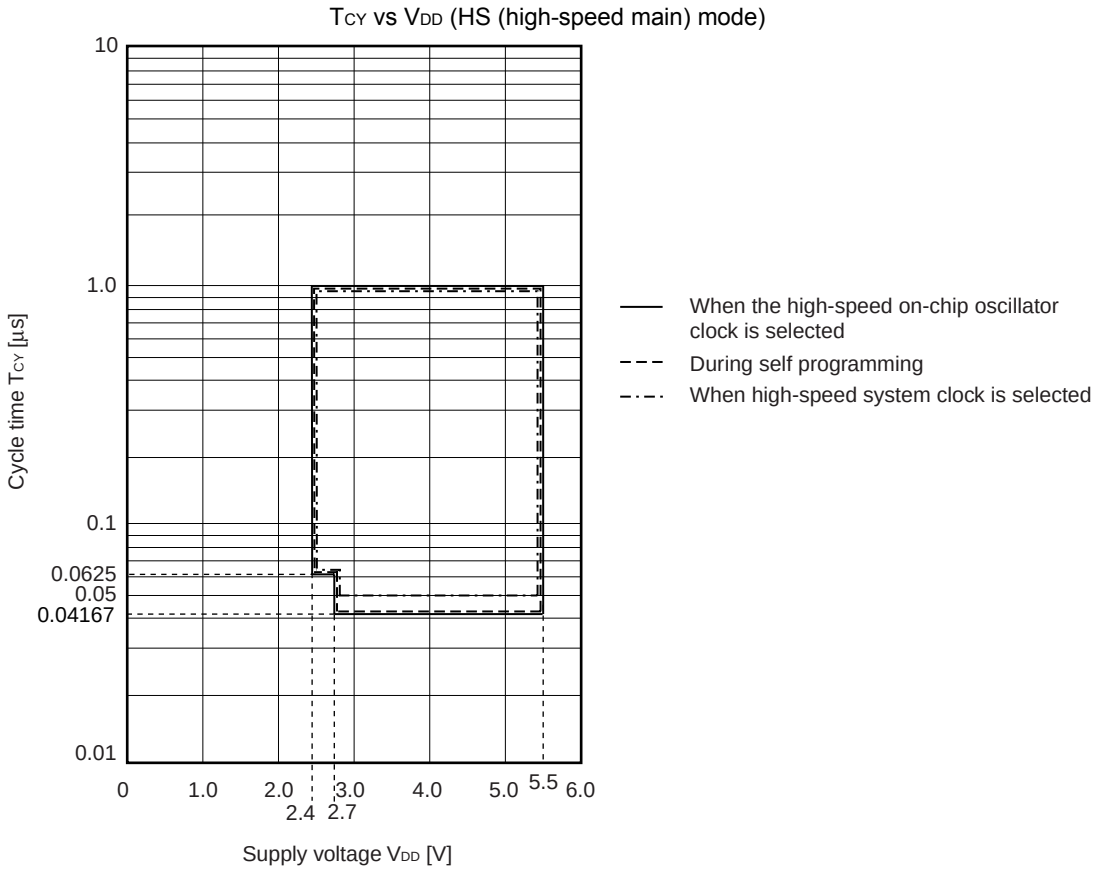
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (2/2)

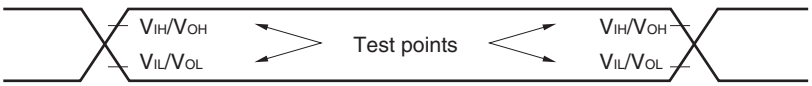
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB operating current	I_{USBH} **Note 11**	During USB communication operation under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): • The internal power supply for the USB is used. • X1 oscillation frequency (f_X) = 12 MHz, PLL oscillation frequency (f_{PLL}) = 48 MHz • The host controller (via two ports) is set to operate in full-speed mode with four pipes (end points) used simultaneously. (PIPE4: Bulk OUT transfer (64 bytes), PIPE5: Bulk IN transfer (64 bytes), PIPE6: Interrupt OUT transfer, PIPE7: Interrupt IN transfer). • The USB ports (two ports) are individually connected to a peripheral function via a 0.5 m USB cable.		9.0		mA
	I_{USBF} **Note 11**	During USB communication operation under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): • The internal power supply for the USB is used. • X1 oscillation frequency (f_X) = 12 MHz, PLL oscillation frequency (f_{PLL}) = 48 MHz • The function controller is set to operate in full-speed mode with four pipes (end points) used simultaneously. (PIPE4: Bulk OUT transfer (64 bytes), PIPE5: Bulk IN transfer (64 bytes), PIPE6: Interrupt OUT transfer, PIPE7: Interrupt IN transfer). • The USB port (one port) is connected to the host device via a 0.5 m USB cable.		2.5		mA
	I_{SUSP} **Note 12**	During suspended state under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): • The function controller is set to full-speed mode (the UDP0 pin is pulled up). • The internal power supply for the USB is used. • The system is set to STOP mode (When the high-speed on-chip oscillator, high-speed system clock, and subsystem clock are stopped. When the watchdog timer is stopped.). • The USB port (one port) is connected to the host device via a 0.5 m USB cable.		240		μA

(**Notes** and **Remarks** are listed on the next page.)

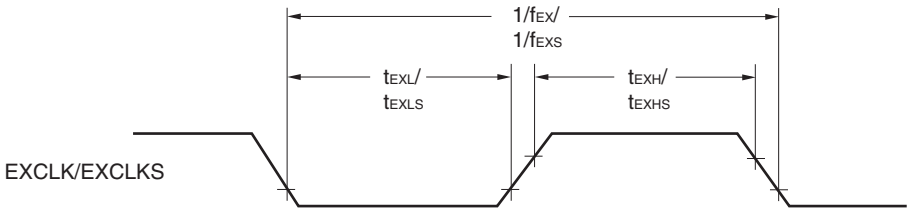
Minimum Instruction Execution Time during Main System Clock Operation



AC Timing Test Points



External System Clock Timing



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V ≤ V_{DD} ≤ 5.5 V	167			ns
			2.4 V ≤ V_{DD} ≤ 5.5 V	250			ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 – 12			ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 – 18			ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2 – 38			ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V		44			ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		44			ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		75			ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			19			ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4				25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 0, 3, 5, 7)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
SCKp cycle time Note 5	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}			ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}			ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	16 MHz < f_{MCK}	8/f_{MCK}			ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}			ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		6/f_{MCK} and 500			ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2 – 7			ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2 – 8			ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2 – 18			ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+20			ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+30			ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+31			ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+31			ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 5.5 V			2/f_{MCK}+44	ns
			2.4 V ≤ V_{DD} ≤ 5.5 V			2/f_{MCK}+75	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SOp output lines.

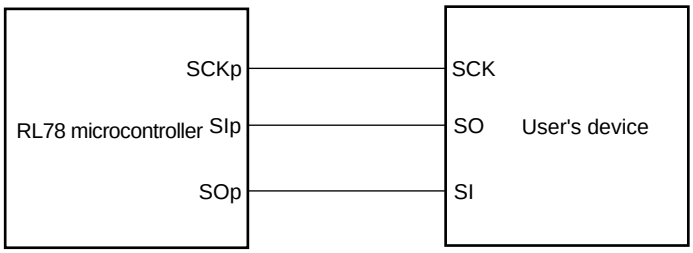
5. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

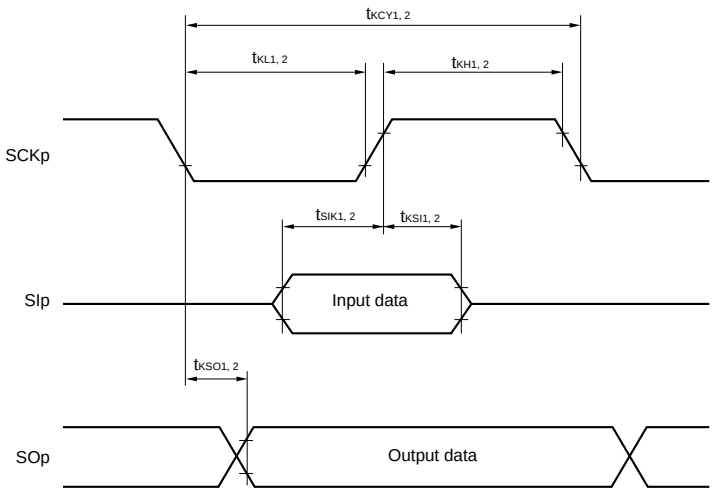
Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0),
n: Channel number (n = 0, 1), g: PIM number (g = 0, 3, 5, 7)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

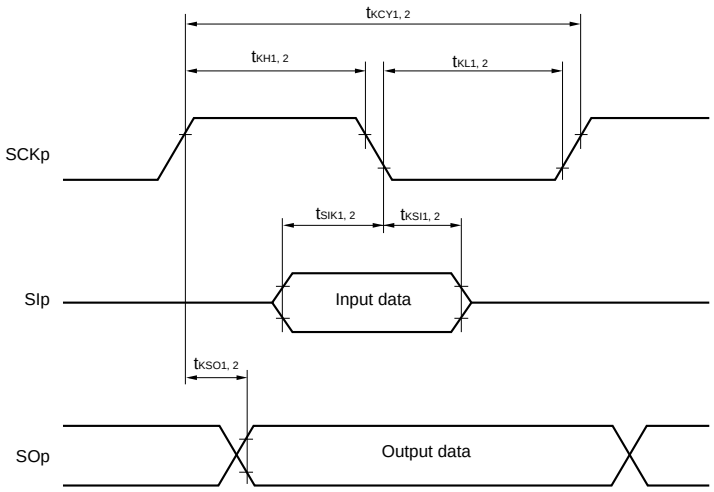
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01)

2. m: Unit number, n: Channel number (mn = 00, 01)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200			ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300			ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		$t_{KCY1}/2 - 50$			ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 120$			ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		$t_{KCY1}/2 - 7$			ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 10$			ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58			ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121			ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10			ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10			ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ				60	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ				130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23			ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33			ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10			ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10			ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ				10	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ				10	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(**Caution** and **Remark** are listed on the next page.)

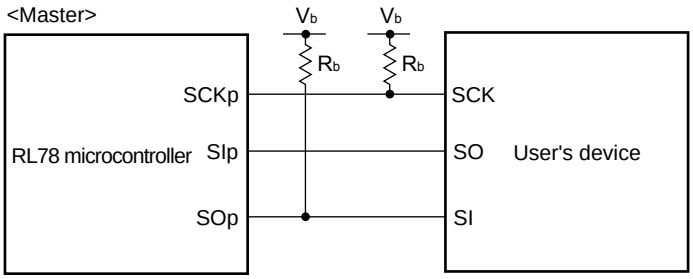
Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3 Use it with $V_{DD} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

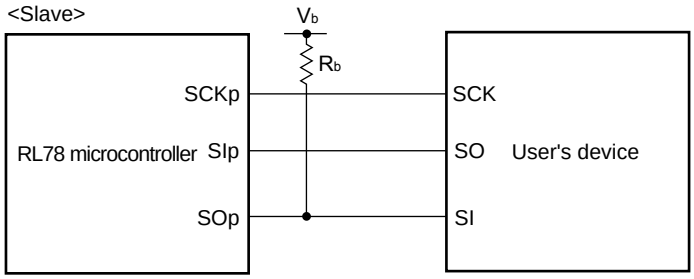
2. p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00))

4. CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00))

4. CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.

(3) I^2C fast mode plus

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode plus: f_{CLK} ≥ 10 MHz	2.7 V ≤ V_{DD} ≤ 5.5 V	0	1000	kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		μs
Hold time[Note 1]	$t_{HD:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		μs
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.5		μs
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		μs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		50		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0	0.45	μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		μs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.5		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

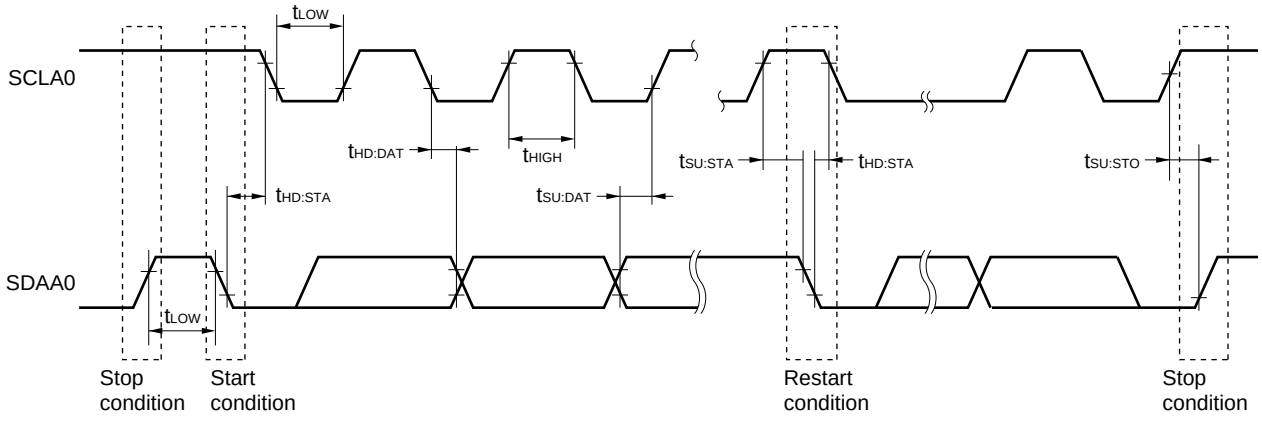
2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 1 (PIOR1) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 kΩ

IICA serial transfer timing



(3) BC option standard (Host)

(T_A = –40 to +85°C, 4.75 V ≤ UV_{BUS} ≤ 5.25 V, 3.0 V ≤ UV_{DD} ≤ 3.6 V, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDPi output voltage (UV_{BUS} divider ratio) • VDOUEi = 1	VDSELi [3:0] (i = 0, 1)	1000	V_{P20}		38	40	42	% UV_{BUS}
		1001	V_{P27}		51.6	53.6	55.6	% UV_{BUS}
		1010	V_{P20}		38	40	42	% UV_{BUS}
		1100	V_{P33}		60	66	72	% UV_{BUS}
UDMi output voltage (UV_{BUS} divider ratio) • VDOUEi = 1	VDSELi [3:0] (i = 0, 1)	1000	V_{M20}		38	40	42	% UV_{BUS}
		1001	V_{M20}		38	40	42	% UV_{BUS}
		1010	V_{M27}		51.6	53.6	55.6	% UV_{BUS}
		1100	V_{M33}		60	66	72	% UV_{BUS}
UDPi comparing voltage Note 1 (UV_{BUS} divider ratio) • VDOUEi = 1 • CUSDETEi = 1	VDSELi [3:0] (i = 0, 1)	1000	V_{HDETP_UP0}	The rise of pin voltage detection voltage	56.2			% UV_{BUS}
			V_{HDETP_DWN0}	The fall of pin voltage detection voltage			29.4	% UV_{BUS}
		1001	V_{HDETP_UP1}	The rise of pin voltage detection voltage	60.5			% UV_{BUS}
			V_{HDETP_DWN1}	The fall of pin voltage detection voltage			45.0	% UV_{BUS}
		1010	V_{HDETP_UP2}	The rise of pin voltage detection voltage	56.2			% UV_{BUS}
			V_{HDETP_DWN2}	The fall of pin voltage detection voltage			29.4	% UV_{BUS}
UDMi comparing voltage Note 1 (UV_{BUS} divider ratio) • VDOUEi = 1 • CUSDETEi = 1	VDSELi [3:0] (i = 0, 1)	1000	V_{HDETM_UP0}	The rise of pin voltage detection voltage	56.2			% UV_{BUS}
			V_{HDETM_DWN0}	The fall of pin voltage detection voltage			29.4	% UV_{BUS}
		1001	V_{HDETM_UP1}	The rise of pin voltage detection voltage	56.2			% UV_{BUS}
			V_{HDETM_DWN1}	The fall of pin voltage detection voltage			29.4	% UV_{BUS}
		1010	V_{HDETM_UP2}	The rise of pin voltage detection voltage	60.5			% UV_{BUS}
			V_{HDETM_DWN2}	The fall of pin voltage detection voltage			45.0	% UV_{BUS}
UDPi pull-up detection Note 2 Connect detection with the full speed function (pull-up resistor)		1000 1001 1010	R_{HDET_PULL}	In full-speed mode, the power supply voltage range of pull-up resistors connected to the USB function module is between 3.0 V and 3.6 V.			1.575	kΩ
UDMi pull-up detection Note 2 Connect detection with the low-speed (pull-up resistor)		1000 1001 1010	R_{HDET_PULL}	In low-speed mode, the power supply voltage range of pull-up resistors connected to the USB function module is between 3.0 V and 3.6 V.			1.575	kΩ
UDMi sink current detection Note 2 Connect detection with the BC1.2 portable device (sink resistor)		1000 1001 1010	I_{HDET_SINK}		25			μA

Notes 1. If the voltage output from UDPi or UDMi (i = 0, 1) exceeds the range of the MAX and MIN values prescribed in this specification, DPCUSDETi (bit 8) and DMCUSDETi (bit 9) of the USBBCOPTi register are set to 1.

2. If the pull-up resistance or sink current prescribed in this specification is applied to UDPi or UDMi (i = 0, 1), DPCUSDETi (bit 8) and DMCUSDETi (bit 9) of the USBBCOPTi register are set to 1.

Remark i = 0, 1

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = –40 to +85°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD0}	Power supply rise time	3.98	4.06	4.14	V
			Power supply fall time	3.90	3.98	4.06	V
		V_{LVD1}	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time		t_{LD}				300	μs

3. ELECTRICAL SPECIFICATIONS (G: T_A = -40 to +105°C)

This chapter describes the electrical specifications for the products "G: Industrial applications (T_A = -40 to +105°C)".

The target products G: Industrial applications ; T_A = -40 to +105°C
R5F10JBCGNA, R5F10JBCGFP, R5F10JGCGNA, R5F10JGCGFB,
R5F10KBCGNA, R5F10KBCGFP, R5F10KGCGNA, R5F10KGCGFB

Cautions 1. The RL78 microcontrollers has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. The pins mounted depend on the product.

3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

There are following differences between the products "G: Industrial applications (T_A = -40 to +105°C)" and the products “A: Consumer applications”.

Parameter	Application	
	A: Consumer applications	G: Industrial applications
Operating ambient temperature	T_A = -40 to +85°C	T_A = -40 to +105°C
High-speed on-chip oscillator clock accuracy	2.4 V ≤ V_{DD} ≤ 5.5 V ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C	2.4 V ≤ V_{DD} ≤ 5.5 V ±2.0%@ T_A = +85 to +105°C ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C
Serial array unit	UART CSI: f_{CLK}/2 (supporting 16 Mbps), f_{CLK}/4 Simplified I^2C communication	UART CSI: f_{CLK}/4 Simplified I^2C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products “A: Consumer applications”. For details, refer to **3.1** to **3.10**.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	MHz
XT1 clock oscillation frequency (f_{XT})Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

3.2.2 On-chip oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{HOCO}		1		48	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85 °C	–1.0		+1.0	%
		–40 to –20 °C	–1.5		+1.5	%
		+85 to +105 °C	–2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	f_{IL}			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			–15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

3.2.3 PLL oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	f_{PLLIN}	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	f_{PLL}			48.00		MHz
Lock up time		From PLL output enable to stabilization of the output frequency	40.00			μs
Interval time		From PLL stop to PLL re-operation setteing Wait time	4.00			μs
Setting wait time		From after PLL input clock stabilization and PLL setting is fixed to start setting Wait time required	1.00			μs

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P130, P140	2.4V ≤ V_{DD} ≤ 5.5 V			8.5 Note 2	mA
		Per pin for P60 to P63	2.4V ≤ V_{DD} ≤ 5.5 V			15.0 Note 2	mA
		Total of P00, P01, P40, P41, P120, P130, P140 (When duty ≤ 70% Note 3)	4.0 V ≤ V_{DD} ≤ 5.5 V			40.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			15.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			9.0	mA
		Total of P14 to P17, P30, P31, P50, P51, P60 to P63, P70 to P75 (When duty ≤ 70% Note 3)	4.0 V ≤ V_{DD} ≤ 5.5 V			40.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			35.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.4V ≤ V_{DD} ≤ 5.5 V			80.0	mA
	I_{OL2}	Per pin for P20 to P27	2.4V ≤ V_{DD} ≤ 5.5 V			0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.4V ≤ V_{DD} ≤ 5.5 V			5.0	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty ratio to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA
Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (High-speed main) mode Note 9	f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.67	2.25	mA
					V_{DD} = 3.0 V		0.67	2.25	mA
				f_{HOCO} = 24 MHz Note 7, f_{IH} = 12 MHz Note 4	V_{DD} = 5.0 V		0.50	1.55	mA
					V_{DD} = 3.0 V		0.50	1.55	mA
				f_{HOCO} = 12 MHz Note 7, f_{IH} = 6 MHz Note 4	V_{DD} = 5.0 V		0.41	1.21	mA
					V_{DD} = 3.0 V		0.41	1.21	mA
				f_{HOCO} = 6 MHz Note 7, f_{IH} = 3 MHz Note 4	V_{DD} = 5.0 V		0.37	1.05	mA
					V_{DD} = 3.0 V		0.37	1.05	mA
			HS (High-speed main) mode Note 9	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.28	1.90	mA
					Resonator connection		0.45	2.00	mA
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.28	1.90	mA
					Resonator connection		0.45	2.00	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.19	1.02	mA
					Resonator connection		0.26	1.10	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.19	1.02	mA
					Resonator connection		0.26	1.10	mA
			HS (High-speed main) mode (PLL operation) Note 9	f_{PLL} = 48 MHz, f_{CLK} = 24 MHz Note 3	V_{DD} = 5.0 V		0.91	2.74	mA
					V_{DD} = 3.0 V		0.91	2.74	mA
				f_{PLL} = 48 MHz, f_{CLK} = 12 MHz Note 3	V_{DD} = 5.0 V		0.85	2.31	mA
					V_{DD} = 3.0 V		0.85	2.31	mA
				f_{PLL} = 48 MHz, f_{CLK} = 6 MHz Note 3	V_{DD} = 5.0 V		0.82	2.07	mA
					V_{DD} = 3.0 V		0.82	2.07	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = –40°C	Square wave input		0.25	0.57	µA
					Resonator connection		0.44	0.76	µA
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.30	0.57	µA
					Resonator connection		0.49	0.76	µA
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.33	1.17	µA
					Resonator connection		0.63	1.36	µA
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.46	1.97	µA
					Resonator connection		0.76	2.16	µA
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		0.97	3.37	µA
					Resonator connection		1.16	3.56	µA
				f_{SUB} = 32.768 kHz Note 5, T_A = +105°C	Square wave input		3.01	15.37	µA
					Resonator connection		3.20	15.56	µA
	I_{DD3} Note 6	STOP mode Note 8	T_A = –40°C				0.18	0.50	µA
			T_A = +25°C				0.23	0.50	µA
			T_A = +50°C				0.26	1.10	µA
			T_A = +70°C				0.29	1.90	µA
			T_A = +85°C				0.90	3.30	µA
			T_A = +105°C				2.94	15.30	µA

(**Notes** and **Remarks** are listed on the next page.)

(3) Reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), Reference voltage (–) = V_{SS} (ADREFM = 0), target ANI pin : ANI0 to ANI7, ANI16, ANI17, ANI19, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Notes 1, 2	AINL	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	tCONV	10-bit resolution Target ANI pin : ANI0 to ANI7, ANI16, ANI17, ANI19	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target ANI pin : Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI7, ANI16, ANI17, ANI19		0		V_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} Note 3			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} Note 3			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

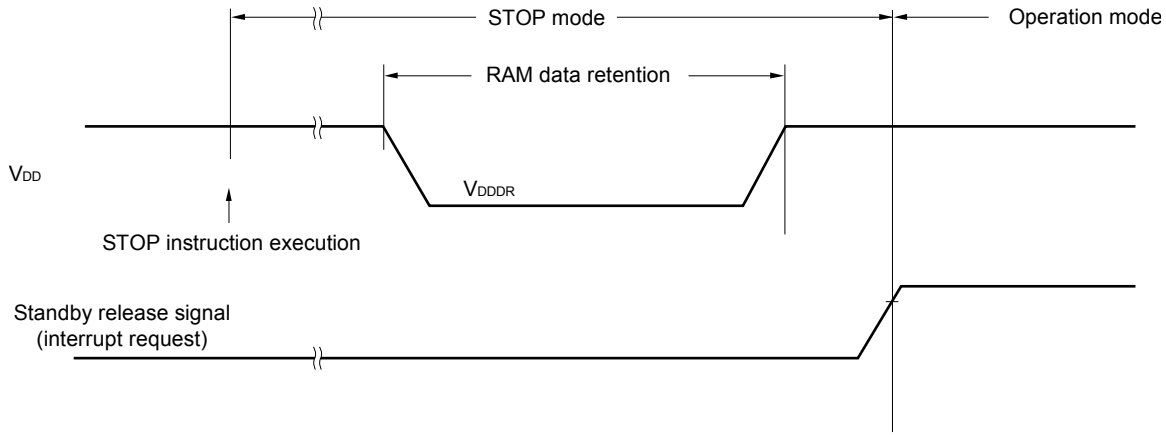
<R> 3.7 RAM Data Retention Characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.

<R>



3.8 Flash Memory Programming Characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	2.4 V ≤ V_{DD} ≤ 5.5 V	1		24	MHz
<R> Number of code flash rewrites	C_{erwr}	Retaining years: 20 years T_A = +85°C Note 4	1,000			Times
<R> Number of data flash rewrites Notes 1, 2, 3		Retaining years: 1 year T_A = +25°C Note 4		1,000,000		
<R>		Retaining years: 5 years T_A = +85°C Note 4	100,000			
<R>		Retaining years: 20 years T_A = +85°C Note 4	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library.

3. These specifications show the characteristics of the flash memory and the results obtained from Renesas Electronics reliability testing.

<R> **4.** This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

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